Panasonic

NP0G3D2

Silicon PNP epitaxial planar transistor (Tr1) Silicon NPN epitaxial planar transistor (Tr2)

For digital circuits

■ Features

- Two elements incorporated into one package
- Suitable for high density package and downsizing of the equipment
- Automatic insertion with the taping is possible

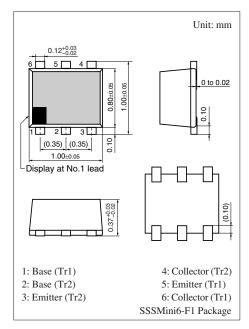
■ Basic Part Number of Element

• UNR31AT × UNR32AL

■ Absolute Maximum Ratings $T_a = 25$ °C

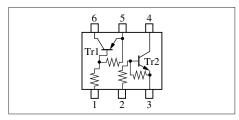
| | Parameter | Symbol | Rating | Unit | |
|---------|------------------------------|------------------|-------------|------|--|
| Tr1 | Collector to base voltage | V_{CBO} | -50 | V | |
| | Collector to emitter voltage | V _{CEO} | -50 | V | |
| | Collector current | I_C | -80 | mA | |
| Tr2 | Collector to base voltage | V_{CBO} | 50 | V | |
| | Collector to emitter voltage | V_{CEO} | 50 | V | |
| | Collector current | I_C | 80 | mA | |
| Overall | Total power dissipation * | P_{T} | 125 | mW | |
| | Junction temperature | T_{j} | 125 | °C | |
| | Storage temperature | T_{stg} | -55 to +125 | °C | |

Note) *: Measuring on substrate at 17 mm \times 10 mm \times 1 mm



Marking Symbol: 3B

Internal Connection



\blacksquare Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr1

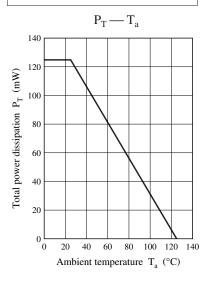
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|------|------|--------|------|
| Collector to base voltage | V_{CBO} | $I_{\rm C} = -10 \; \mu \text{A}, I_{\rm E} = 0$ | -50 | | | V |
| Collector to emitter voltage | V _{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -50 | | | V |
| Collector cutoff current | I_{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | | | - 0.1 | μΑ |
| | I _{CEO} | $V_{CE} = -50 \text{ V}, I_{B} = 0$ | | | - 0.5 | |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -6 \text{ V}, I_C = 0$ | | | - 0.2 | mA |
| Forward current transfer ratio | h _{FE} | $V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$ | 80 | | 400 | _ |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$ | | | - 0.25 | V |
| High level output voltage | V_{OH} | $V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | -4.9 | | | V |
| Low level output voltage | V _{OL} | $V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | - 0.2 | V |
| Input resistance | R_1 | | -30% | 22 | +30% | kΩ |
| Resistance ratio | R_1 / R_2 | | | 0.47 | | _ |
| Gain bandwidth product | f_T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

• Tr2

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|------|-----|------|------|
| Collector to base voltage | V_{CBO} | $I_{\rm C} = 10 \; \mu \text{A}, \; I_{\rm E} = 0$ | 50 | | | V |
| Collector to emitter voltage | V _{CEO} | $I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$ | 50 | | | V |
| Collector cutoff current | I_{CBO} | $V_{CB} = 50 \text{ V}, I_{E} = 0$ | | | 0.1 | μΑ |
| | I _{CEO} | $V_{CE} = 50 \text{ V}, I_{B} = 0$ | | | 0.5 | |
| Emitter cutoff current | I_{EBO} | $V_{EB} = 6 \text{ V}, I_{C} = 0$ | | | 2.0 | mA |
| Forward current transfer ratio | h _{FE} | $V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$ | 20 | | | _ |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$ | | | 0.25 | V |
| High level output voltage | V _{OH} | $V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | 4.9 | | | V |
| Low level output voltage | V _{OL} | $V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | 0.2 | V |
| Input resistance | R_1 | | -30% | 4.7 | +30% | kΩ |
| Resistance ratio | R_1 / R_2 | | 0.8 | 1.0 | 1.2 | _ |
| Gain bandwidth product | f_T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

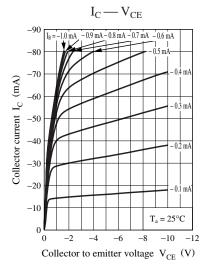
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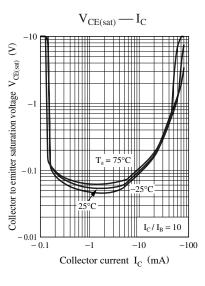
Common characteristics chart

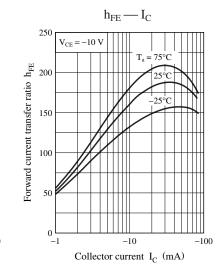


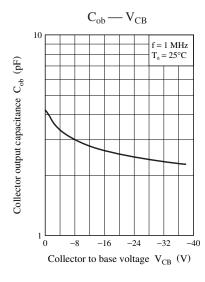
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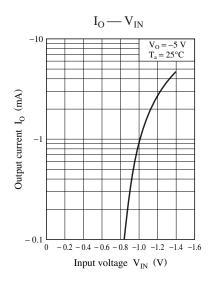
Characteristics charts of Tr1

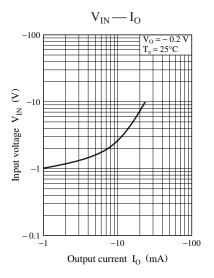






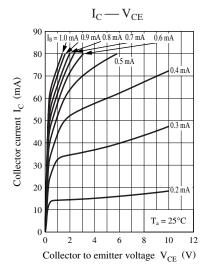


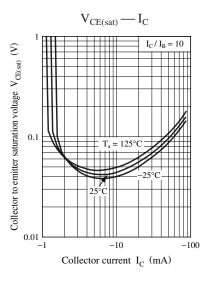


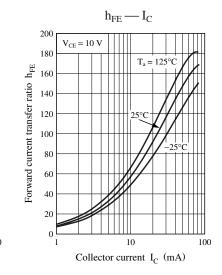


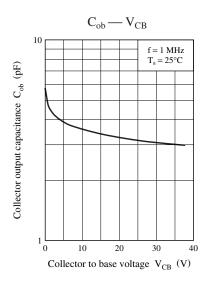
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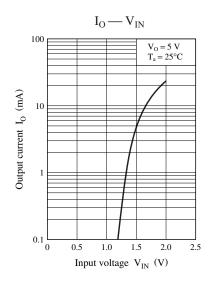
Characteristics charts of Tr2

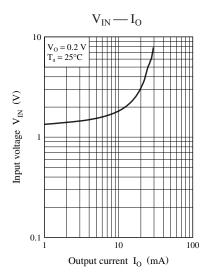












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